

71A
4-10-02
R. Grader

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO. 025311/0105



Applicant: Ichiro OKABE *et al.*

Title: METHOD OF FORMING A FINE PATTERN, AND METHOD OF
MANUFACTURING A SEMICONDUCTOR DEVICE, AND A
SEMICONDUCTOR DEVICE HAVING A FINE PATTERN

Appl. No.: 09/597,161

Filing Date: 06/20/2000

Examiner: J. Diaz

Art Unit: 2815

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AMENDMENT AND REPLY UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed October 3, 2001, please amend the application as follows:

In the Title:

Please replace the title with: "Method of Forming a Fine Pattern Using a Silicon-Oxide-Based Film, Semiconductor Device with a Silicon-Oxide-Based Film and Method of Manufacture Thereof."

In the Claims:

Please substitute for original claims 1-5 the following amended versions of the same claims. The changes are explicitly shown in the attached Appendix A, "Version with Markings to Show Changes Made."